

### INCHANGE SEMICONDUCTOR

### isc Silicon NPN Power Transistor

# 2SC2137

### DESCRIPTION

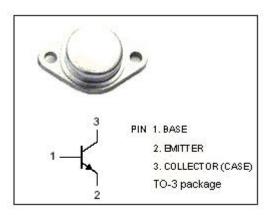
- High Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub>= 400V (Min)
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

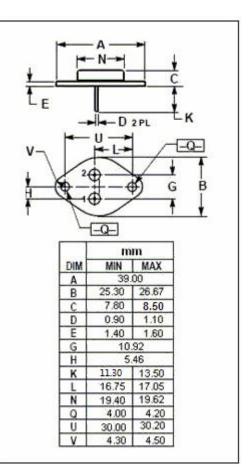
### **APPLICATIONS**

- Switching regulator and high voltage switching applications.
- · High speed DC-DC converter applications.

#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	MBOL PARAMETER		UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	500	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
Ic	Collector Current-Continuous	7	А	
IB	Base Current-Continuous	2	А	
Pc	Collector Power Dissipation @T <sub>c</sub> =25℃	80	W	
Tj	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C	





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#### **ELECTRICAL CHARACTERISTICS**

#### $T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	400			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	500			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.3A			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.3A			2.0	V
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	10			
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 400V; I <sub>E</sub> = 0			0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			1.0	mA

#### Switching Times

tr	Rise Time	V <sub>CC</sub> = 200V; I <sub>B1</sub> = -I <sub>B2</sub> = 0.3A; R <sub>L</sub> = 40 Ω		1.0	μs
tstg	Storage Time			2.0	μs
t <sub>f</sub>	Fall Time			1.0	μs

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